1/9 M. Angelopoulos et al. D.P.M. YOR920010135US1

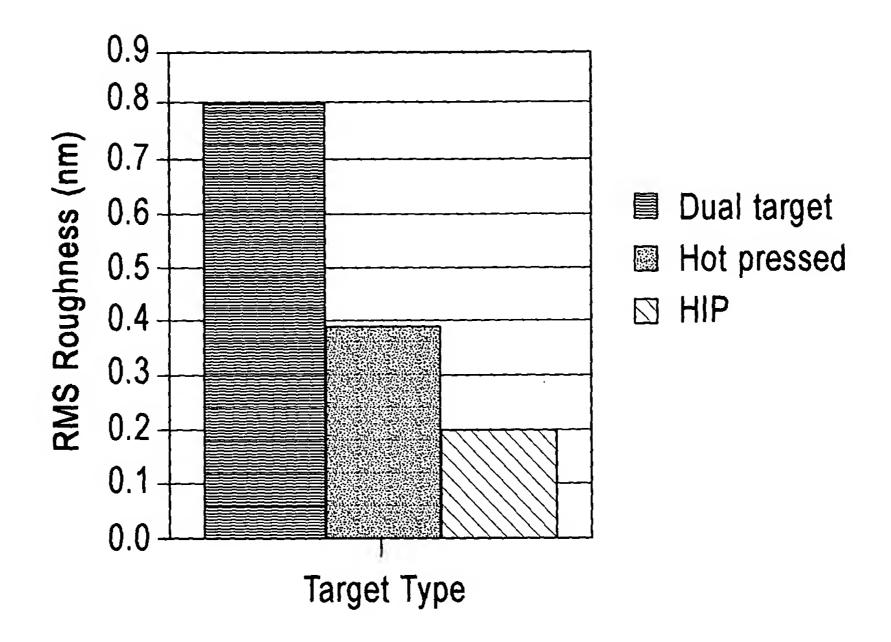


Fig. 1

Embodiment ID	Ar Pressure (mT)	Ar flow (sccm)	N <sub>2</sub> flow (sccm)	Thickness (Å)	Si(at.%)	Ti(AT.%)	N(at.%)	O(at.%)
1	1	15	6	913	40.6	3.8	55.3	0.3
2	1	15	7.5	812	39.7	3.5	56.4	0.5
3	1	15	9	739	39.2	3.3	57.1	0.36
4	2	15	6	838	39.1	3.6	56.3	0.96
5	2	15	. 9	667	38.5	3.3	56.2	1.97
6	5	15	6	761	36.5	3.5	47.3	12.74
7	5	15	7.5	635	36.7	3.5	42.3	17.5
8	5	15	9	580	37.1	3.4	46.2	13.35

Fig. 2

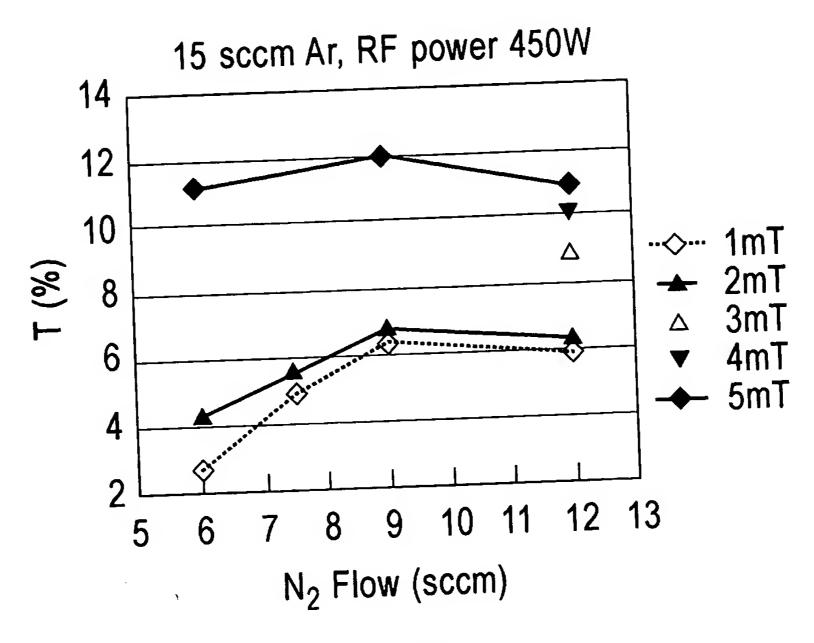


Fig. 3A

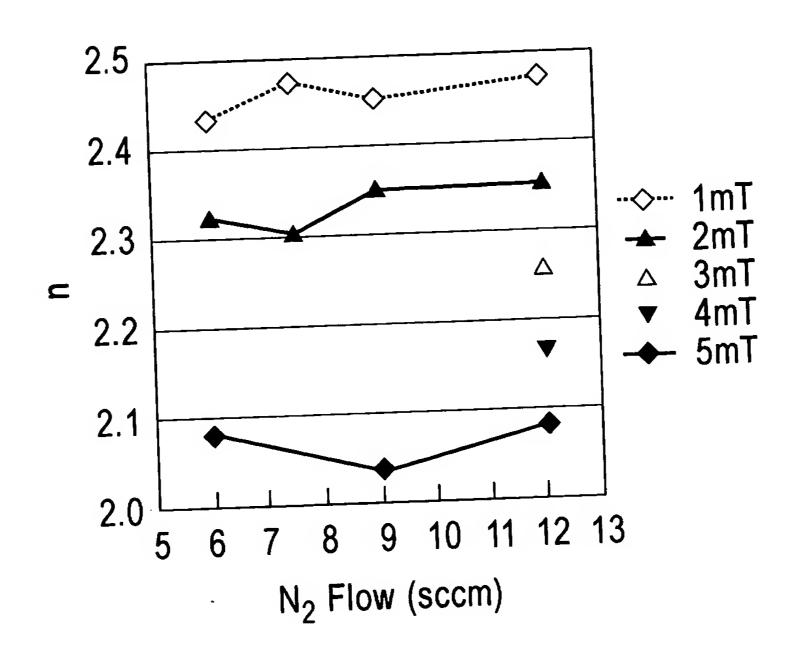


Fig. 3B

3/9 M. Angelopoulos et al. D.P.M. YOR920010135US1

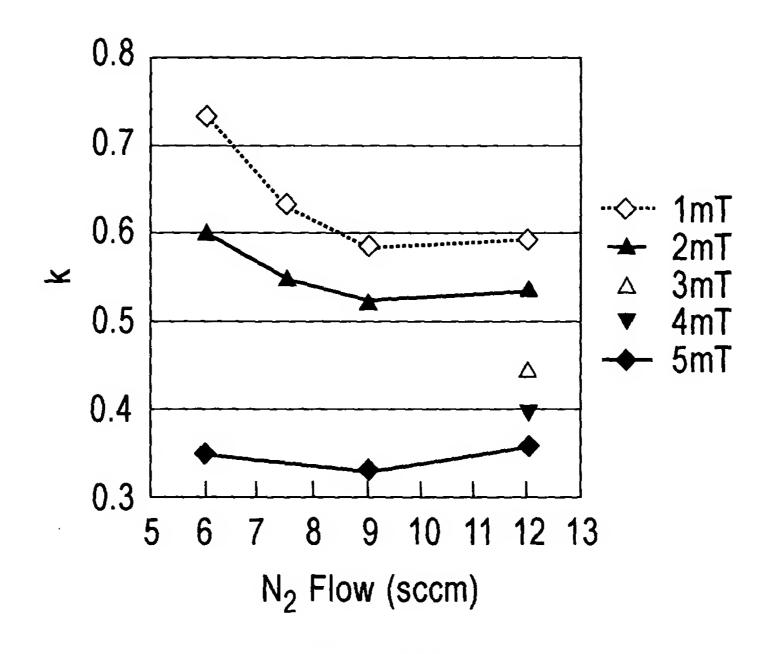
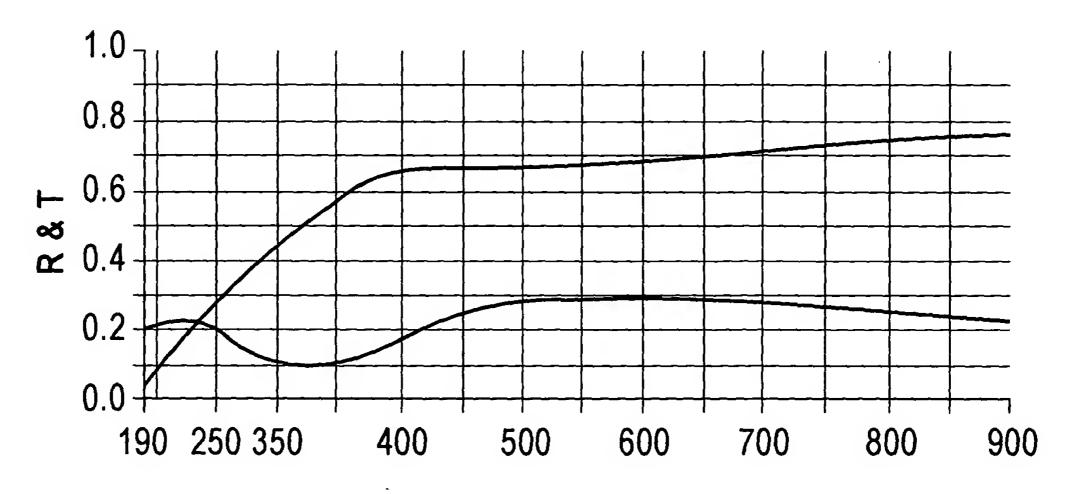


Fig. 3C



Thickness	T@193nm	R@193nm	PS@193nm	T@248nm	T@365nm
679A	5.72%	21%	183.1 deg	27%	60%

Fig. 4

4/9 M. Angelopoulos et al. D.P.M. YOR920010135US1

Estimated Relative Composition in Atom Percent, Sample Description	from C	ESCA S	Surface 0	Survey <b>Si</b>	Scans <b>Ti</b>
Surface compositions  Embodiment 9: 690Å thick film, as-deposited (1 mT, N <sub>2</sub> flow 9 sccm)	7.4	36.3	21.6	32.0	2.2
Embodiment 9-annealed: 690Å thick film, annealed in air, 225°C, 15 minutes	5.5	34.9	24.3	32.0	2.3
Embodiment 10: 890Å thick film, as-deposited (5 mT, N <sub>2</sub> flow 9 sccm)	12.2	28.1	29.8	27.7	2.0
Embodiment 10-annealed: 890Å thick film, annealed in air, 225°C, 15 minutes	12.6	26.4	31.8	26.9	2.1
Bulk compositions Embodiment 9: 690Å thick film, as-deposited (1 mT, N <sub>2</sub> flow 9 sccm)	<1	54.1	<1	41.6	3.3
Embodiment 9-annealed: 690Å thick film, annealed in air, 225°C, 15 minutes	<1	52.4	<1	41.9	4.4
Embodiment 10: 890Å thick film, as-deposited (5 mT, N <sub>2</sub> flow 9 sccm)	<1	40.3	16.3	39.1	4.3
Embodiment 10-annealed: 890Å thick film, annealed in air, 225°C, 15 minutes	<1	38.3	17.4	40.2	4.0

Fig. 5A

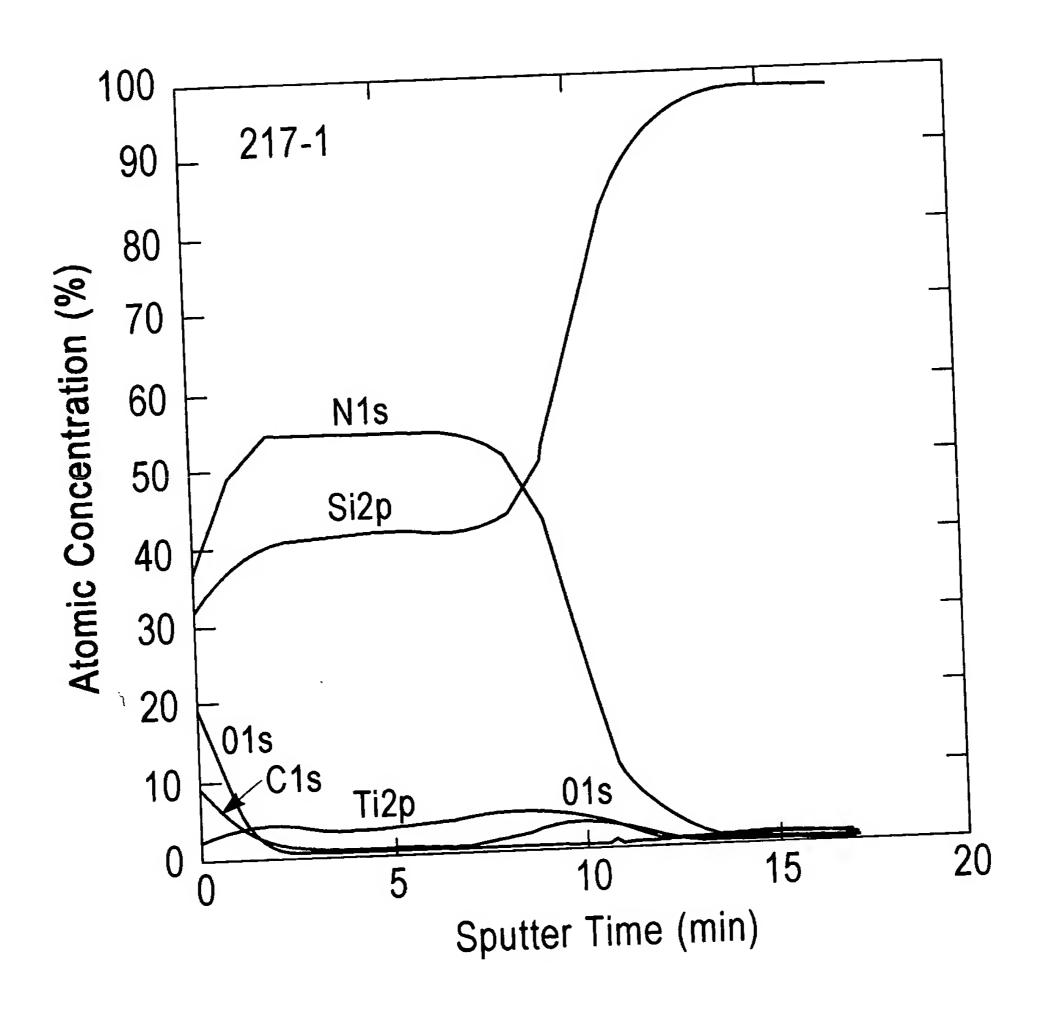


Fig. 5B

## 6/9 M. Angelopoulos et al. D.P.M. YOR920010135US1

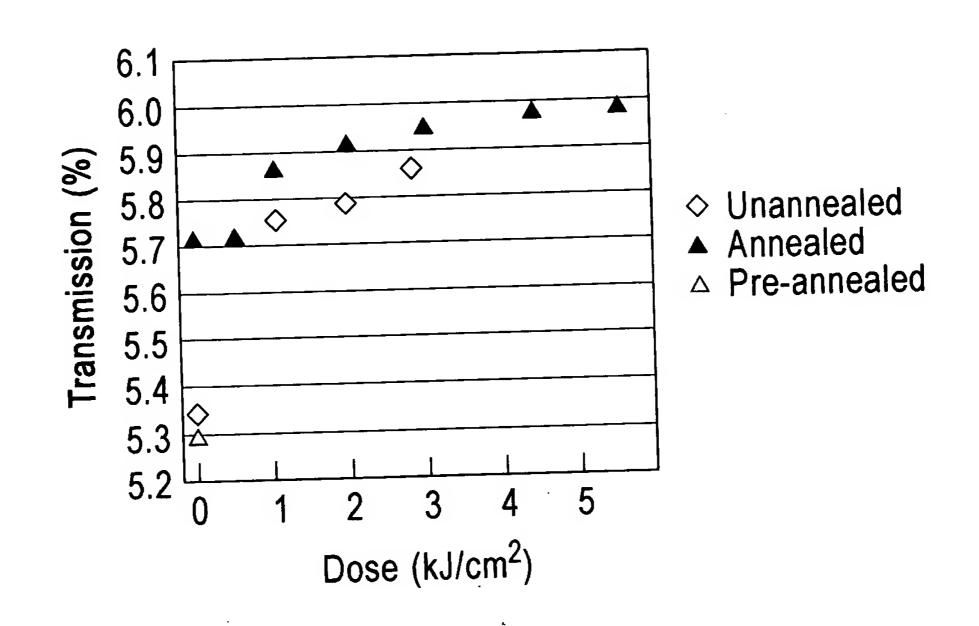
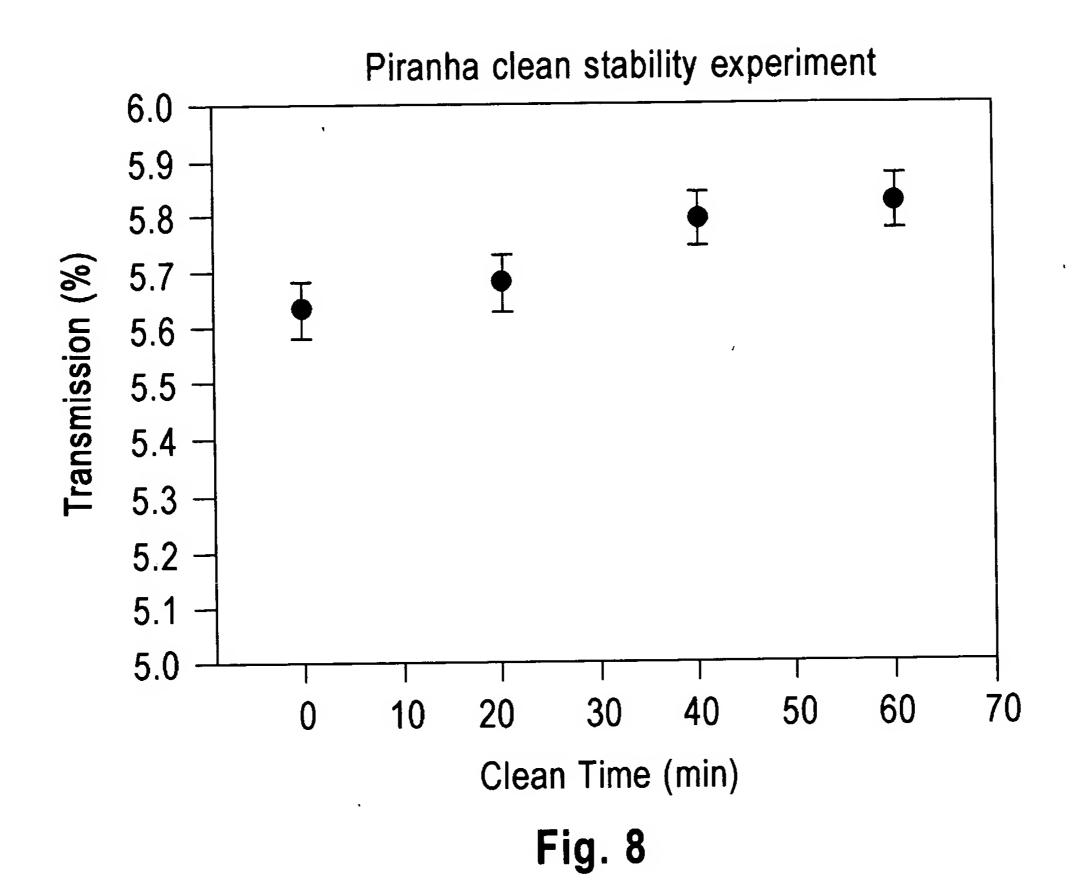


Fig. 6

	Air anneal 225°C, 15 min	N <sub>2</sub> anneal 225°C 15 min	Oxygen plasma (200W, 60min)
%T (initial)	5.61	5.6	5.60
%T (after treatment)	6.11	5.9	2 6.12
%T change after laser	0.27% after	0.32% after	-
irradiation	5.4 kJ/cm <sup>2</sup>	2.2 kJ/cm <sup>2</sup>	

Fig. 7



k %T P<sub>O2</sub> 0(%) Ti(%) N(%) t<sub>193nmPS</sub> Si(%) n P<sub>N2</sub> ID  $P_{Ar}$ 193nmPS (Å) (mT) (mT) (mT) 0.24 2.07 21.4 910 30 3.4 30 0.1 36 0.3 11 0.17 1.78 23 19.2 43.7 1,242 3 33.5 0.11 12 0.3 0.11 29 1.58 65.9 1,668 3.2 0.15 29.1 1.4 0.3 13 0.15 20.6 1.62 1,563 65.9 1.8 3.8 0.15 28.8 0.3 14 1

Fig. 9

Embodiment ID	Ti Power (W)	Ar Pressure (mT)	Thickness (Å)	Deposition Time (sec)		Ti(at.%)	N(at.%)	O(at.%)
15	80	2	726	400	40.8	2.5	53	3.27
16	90	2	729	400	39.2	2.9	53.5	4.19
17	120	2	673	400	38.6	4	52.5	4.58
18	80	1	1,169	600	40.5	2.6	55	1.39
19	120	1	1,212	600	38.9	4.2	54.9	1.6

Fig. 10

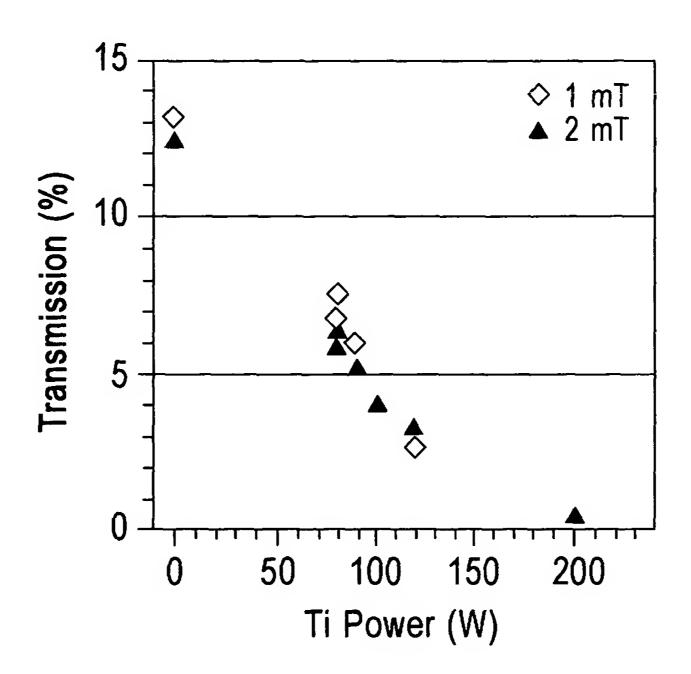


Fig. 11A

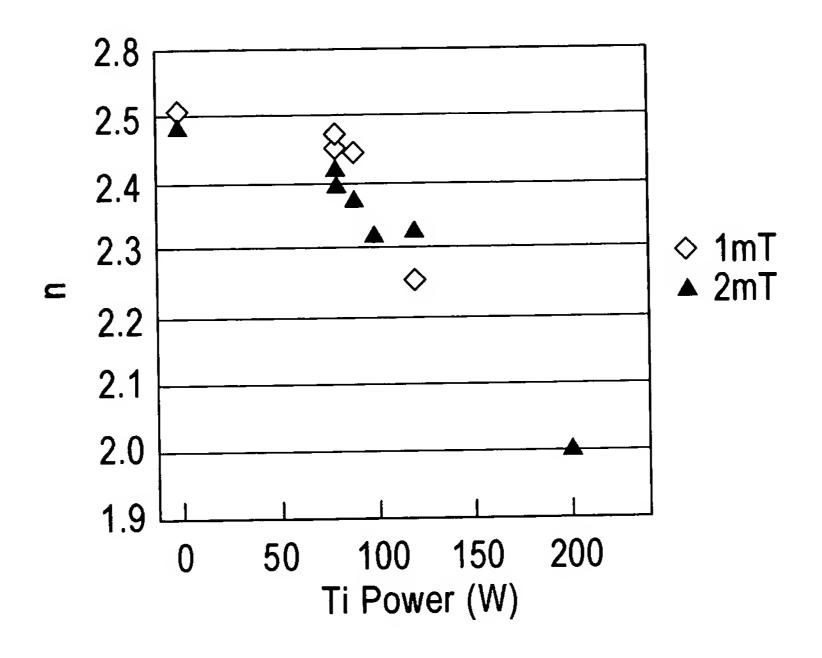


Fig. 11B

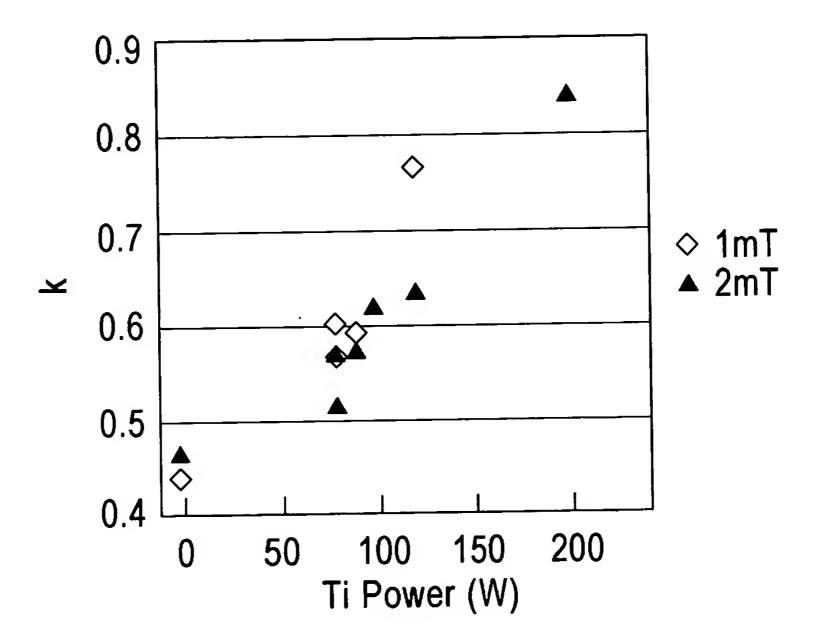


Fig. 11C